

Performance

- Technology: 0.35um Power GaN HEMT
- Frequency: 2.3GHz
- Typical Pout : 49dBm(CW)
- Typical Gain: 10dB
- Typical PAE: 60%
- Bias: 28V/-4~-2V
- Package: Metal Ceramic



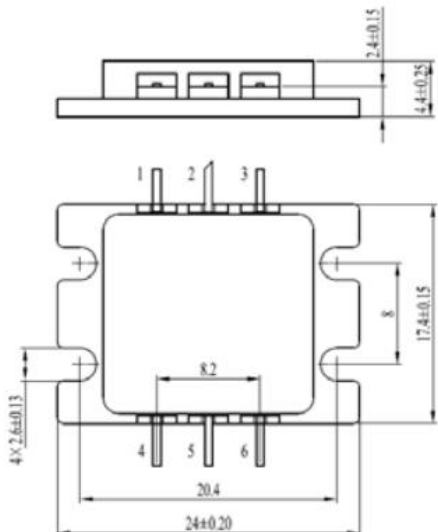
Electrical Specifications (TA=25°C, Vd=28V, CW, F: 2.3GHz)

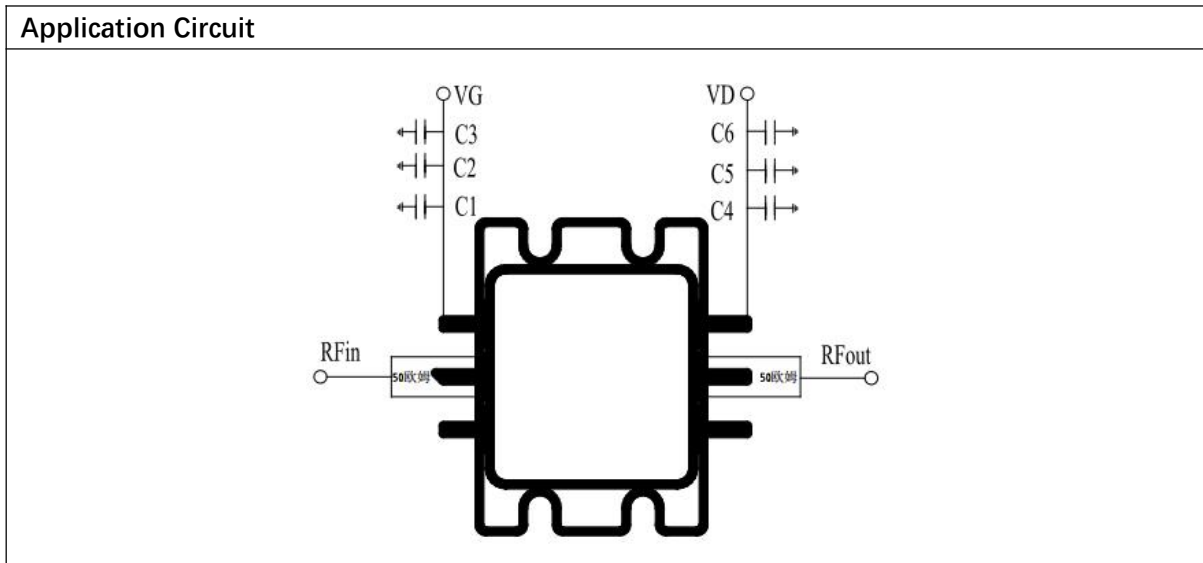
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	49	-	dBm
Gp	Power Gain	-	10	-	dB
η_{add}	Power Added Efficiency		60	-	%
ΔGp	Gain Flatness	-0.5	-	+0.5	dB
Rth	Thermal Resistance	-	-	1.51	°C/W

Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	100W	25°C
Tch	Channel Temperature	175°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Pad Definition												
 The drawing consists of two views: a side view at the top and a top view below it. The side view shows a central pad with three smaller pads on top, with dimensions 2.4±0.15 and 4.4±0.25. The top view shows a central square pad with six pins (1-6) and dimensions 24±0.20, 20.4, 8.2, 17.4±0.15, 8, and 4×2.6±0.13.	<table><tr><th>No</th><th>Function</th><th>No</th><th>Function</th></tr><tr><td>1、3</td><td>Vg</td><td>4、6</td><td>Vd</td></tr><tr><td>2</td><td>RFin</td><td>5</td><td>RFout</td></tr></table>	No	Function	No	Function	1、3	Vg	4、6	Vd	2	RFin	5	RFout
No	Function	No	Function										
1、3	Vg	4、6	Vd										
2	RFin	5	RFout										



Note:

- (1) The typical packaging form is defined as C164-2 shell packaging;
- (2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (3) In order to ensure the good performance of the power module, the capacity value of the power filter and the energy storage capacitor shall be reasonably selected according to the modulation mode during pulse operation;
- (4) C1=C4=100pf, C2=C5=1000pf, C3=47uf, C6=100uf.